

Technische Information / Technical Information

IGBT-Module
IGBT-Modules

FZ 200 R 65 KF1

eupec



Höchstzulässige Werte / Maximum rated values

Elektrische Eigenschaften / Electrical properties

Kollektor-Emitter-Sperrspannung collector-emitter voltage	$T_{vj}=125^{\circ}\text{C}$ $T_{vj}=25^{\circ}\text{C}$ $T_{vj}=-40^{\circ}\text{C}$	V_{CES}	6500 6300 5800	V
Kollektor-Dauergleichstrom DC-collector current	$T_C = 80^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}$	$I_{C,nom.}$ I_C	200 400	A A
Periodischer Kollektor Spitzenstrom repetitive peak collector current	$t_p = 1\text{ ms}$, $T_C = 80^{\circ}\text{C}$	I_{CRM}	400	A
Gesamt-Verlustleistung total power dissipation	$T_C=25^{\circ}\text{C}$, Transistor	P_{tot}	3,8	kW
Gate-Emitter-Spitzenspannung gate-emitter peak voltage		V_{GES}	+/- 20V	V
Dauergleichstrom DC forward current		I_F	200	A
Periodischer Spitzenstrom repetitive peak forw. current	$t_p = 1\text{ ms}$	I_{FRM}	400	A
Grenzlastintegral der Diode I^2t - value, Diode	$V_R = 0\text{V}$, $t_p = 10\text{ms}$, $T_{vj} = 125^{\circ}\text{C}$	I^2t	26	k A ² s
Isolations-Prüfspannung insulation test voltage	RMS, $f = 50\text{ Hz}$, $t = 1\text{ min.}$	V_{ISOL}	10,2	kV
Teilentladungs Aussetzspannung partial discharge extinction voltage	RMS, $f = 50\text{ Hz}$, Q_{PD} typ. 10pC (acc. To IEC 1287)	V_{ISOL}	5,1	kV

Charakteristische Werte / Characteristic values

Transistor / Transistor

			min.	typ.	max.	
Kollektor-Emitter Sättigungsspannung collector-emitter saturation voltage	$I_C = 200\text{A}$, $V_{GE} = 15\text{V}$, $T_{vj} = 25^{\circ}\text{C}$ $I_C = 200\text{A}$, $V_{GE} = 15\text{V}$, $T_{vj} = 125^{\circ}\text{C}$	$V_{CE\text{ sat}}$	-	4,3 5,3	4,9 5,9	V V
Gate-Schwellenspannung gate threshold voltage	$I_C = 35\text{mA}$, $V_{CE} = V_{GE}$, $T_{vj} = 25^{\circ}\text{C}$	$V_{GE(th)}$	6,4	7,0	8,1	V
Gateladung gate charge	$V_{GE} = -15\text{V} \dots +15\text{V}$	Q_G	-	2,8	-	μC
Eingangskapazität input capacitance	$f = 1\text{MHz}$, $T_{vj} = 25^{\circ}\text{C}$, $V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$	C_{ies}	-	28	-	nF
Kollektor-Emitter Reststrom collector-emitter cut-off current	$V_{CE} = 6300\text{V}$, $V_{GE} = 0\text{V}$, $T_{vj} = 25^{\circ}\text{C}$ $V_{CE} = 6500\text{V}$, $V_{GE} = 0\text{V}$, $T_{vj} = 125^{\circ}\text{C}$	I_{CES}	-	0,2 20	-	mA mA
Gate-Emitter Reststrom gate-emitter leakage current	$V_{CE} = 0\text{V}$, $V_{GE} = 20\text{V}$, $T_{vj} = 25^{\circ}\text{C}$	I_{GES}	-	-	400	nA

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date of publication: 2002-07-05

approved by: Dr. Schütze 2002-07-05

revision/Status: Series 1

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Charakteristische Werte / Characteristic values

Transistor / Transistor

			min.	typ.	max.	
Einschaltverzögerungszeit (ind. Last) turn on delay time (inductive load)	$I_C = 200A, V_{CE} = 3600V$	$t_{d,on}$	-	0,75	-	μs
	$V_{GE} = \pm 15V, R_{Gon} = 13\Omega, C_{GE}=22nF, T_{vj} = 25^\circ C,$					
	$V_{GE} = \pm 15V, R_{Gon} = 13\Omega, C_{GE}=22nF, T_{vj} = 125^\circ C,$					
Anstiegszeit (induktive Last) rise time (inductive load)	$I_C = 200A, V_{CE} = 3600V$	t_r	-	0,37	-	μs
	$V_{GE} = \pm 15V, R_{Gon} = 13\Omega, C_{GE}=22nF, T_{vj} = 25^\circ C,$					
	$V_{GE} = \pm 15V, R_{Gon} = 13\Omega, C_{GE}=22nF, T_{vj} = 125^\circ C,$					
Abschaltverzögerungszeit (ind. Last) turn off delay time (inductive load)	$I_C = 200A, V_{CE} = 3600V$	$t_{d,off}$	-	5,50	-	μs
	$V_{GE} = \pm 15V, R_{Goff} = 75\Omega, C_{GE}=22nF, T_{vj} = 25^\circ C,$					
	$V_{GE} = \pm 15V, R_{Goff} = 75\Omega, C_{GE}=22nF, T_{vj} = 125^\circ C,$					
Fallzeit (induktive Last) fall time (inductive load)	$I_C = 200A, V_{CE} = 3600V$	t_f	-	0,40	-	μs
	$V_{GE} = \pm 15V, R_{Goff} = 75\Omega, C_{GE}=22nF, T_{vj} = 25^\circ C,$					
	$V_{GE} = \pm 15V, R_{Goff} = 75\Omega, C_{GE}=22nF, T_{vj} = 125^\circ C,$					
Einschaltverlustenergie pro Puls turn-on energy loss per pulse	$I_C = 200A, V_{CE} = 3600V, V_{GE} = \pm 15V$ $R_{Gon} = 13\Omega, C_{GE}=22nF, T_{vj} = 125^\circ C, L_G = 280nH$	E_{on}	-	1900	-	mJ
Abschaltverlustenergie pro Puls turn-off energy loss per pulse	$I_C = 200A, V_{CE} = 3600V, V_{GE} = \pm 15V$ $R_{Goff} = 75\Omega, C_{GE}=22nF, T_{vj} = 125^\circ C, L_G = 280nH$	E_{off}	-	1200	-	mJ
Kurzschlußverhalten SC Data	$t_p \leq 10\mu sec, V_{GE} \leq 15V, \text{acc to appl.note 2002/05}$ $T_{vj} \leq 125^\circ C, V_{CC}=4400V, V_{CEmax}=V_{CES} - L_{oCE} \cdot di/dt$	I_{SC}	-	1000	-	A
Modulinduktivität stray inductance module		L_{sCE}	-	25	-	nH
Modulleitungswiderstand, Anschlüsse - Chip module lead resistance, terminals - chip		$R_{CC'+EE'}$	-	0,37	-	m Ω

Diode / Diode

			min.	typ.	max.	
Durchlaßspannung forward voltage	$I_F = 200A, V_{GE} = 0V, T_{vj} = 25^\circ C$	V_F	3,0	3,8	4,6	V
	$I_F = 200A, V_{GE} = 0V, T_{vj} = 125^\circ C$			3,9	4,7	V
Rückstromspitze peak reverse recovery current	$I_F = 200A, - di_F/dt = 700A/\mu s$	I_{RM}	-	270	-	A
	$V_R = 3600V, V_{GE} = -10V, T_{vj} = 25^\circ C$					
	$V_R = 3600V, V_{GE} = -10V, T_{vj} = 125^\circ C$					
Sperrverzögerungsladung recovered charge	$I_F = 200A, - di_F/dt = 700A/\mu s$	Q_r	-	180	-	μC
	$V_R = 3600V, V_{GE} = -10V, T_{vj} = 25^\circ C$					
	$V_R = 3600V, V_{GE} = -10V, T_{vj} = 125^\circ C$					
Abschaltenergie pro Puls reverse recovery energy	$I_F = 200A, - di_F/dt = 700A/\mu s$	E_{rec}	-	220	-	mJ
	$V_R = 3600V, V_{GE} = -10V, T_{vj} = 25^\circ C$					
	$V_R = 3600V, V_{GE} = -10V, T_{vj} = 125^\circ C$					

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Thermische Eigenschaften / Thermal properties

			min.	typ.	max.	
Innerer Wärmewiderstand thermal resistance, junction to case	Transistor / transistor, DC	R_{thJC}	-	-	0,033	K/W
	Diode/Diode, DC		-	-	0,063	K/W
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	pro Modul / per Module $\lambda_{Paste} \leq 1 \text{ W/m}^2\text{K} / \lambda_{grease} \leq 1 \text{ W/m}^2\text{K}$	R_{thCK}	-	0,016	-	K/W
Höchstzulässige Sperrschichttemperatur maximum junction temperature		$T_{vj, max}$	-	-	150	°C
Betriebstemperatur Sperrschicht junction operation temperature	Schaltvorgänge IGBT(RBSOA);Diode(SOA) switching operation IGBT(RBSOA);Diode(SOA)	$T_{vj, op}$	-40	-	125	°C
Lagertemperatur storage temperature		T_{stg}	-40	-	125	°C

Mechanische Eigenschaften / Mechanical properties

Gehäuse, siehe Anlage case, see appendix				
Innere Isolation internal insulation			AIN	
Kriechstrecke creepage distance			56	mm
Luftstrecke clearance			26	mm
CTI comperative tracking index			>600	
Anzugsdrehmoment f. mech. Befestigung mounting torque	Schraube /screw M6	M	5	Nm
Anzugsdrehmoment f. elektr. Anschlüsse terminal connection torque	Anschlüsse / terminals M8	M	8 - 10	Nm
Gewicht weight		G	500	g

Mit dieser technischen Information werden Halbleiterbauelemente spezifiziert, jedoch keine Eigenschaften zugesichert.
Sie gilt in Verbindung mit den zugehörigen Technischen Erläuterungen.

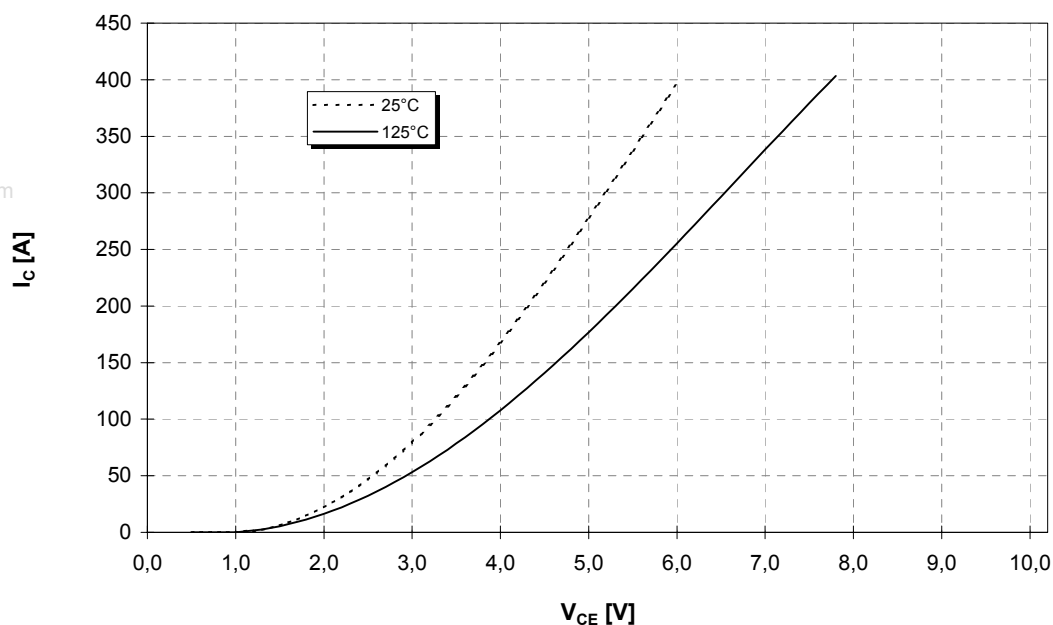
This technical information specifies semiconductor devices but promises no characteristics. It is
valid in combination with the belonging technical notes.



Ausgangskennlinie (typisch)
Output characteristic (typical)

$$I_c = f(V_{CE})$$

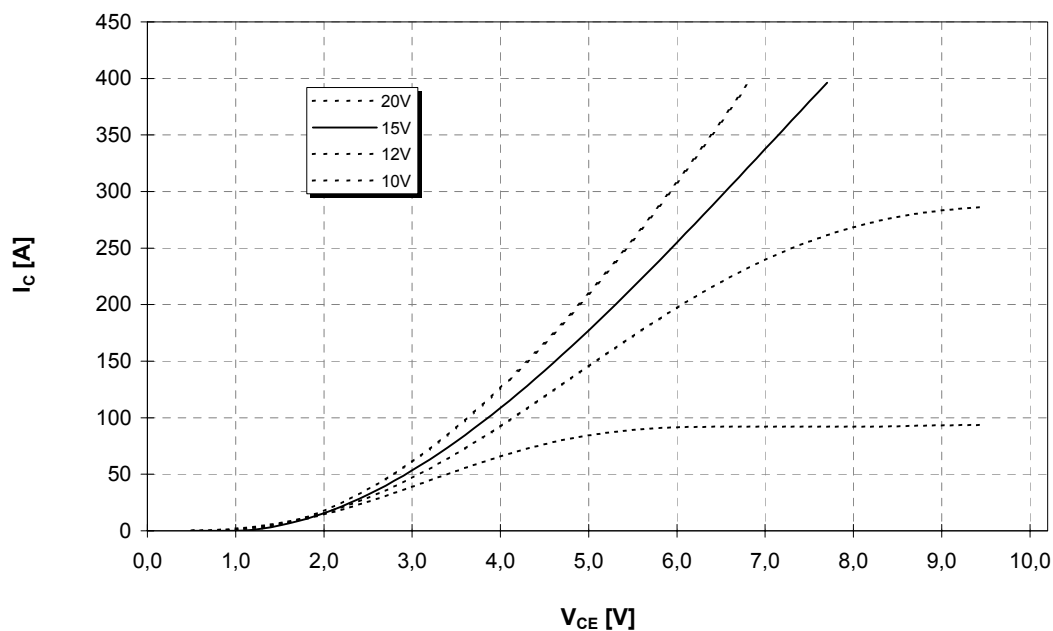
$V_{GE} = 15V$



Ausgangskennlinienfeld (typisch)
Output characteristic (typical)

$$I_c = f(V_{CE}), V_{GE} = \text{< see inset >}$$

$T_{vj} = 125^\circ C$

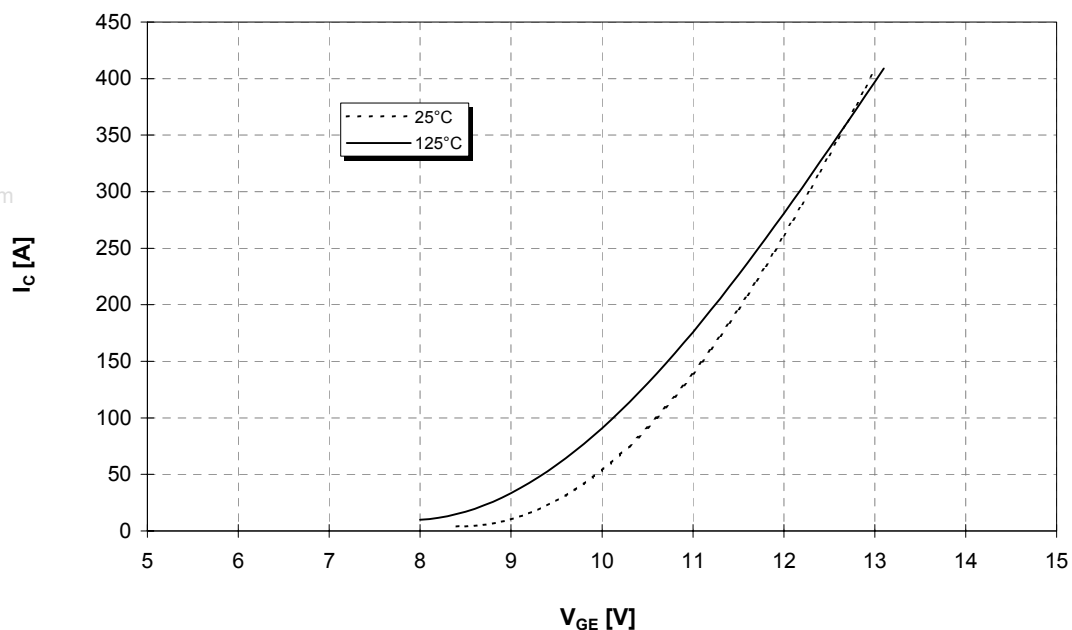




Übertragungscharakteristik (typisch)
Transfer characteristic (typical)

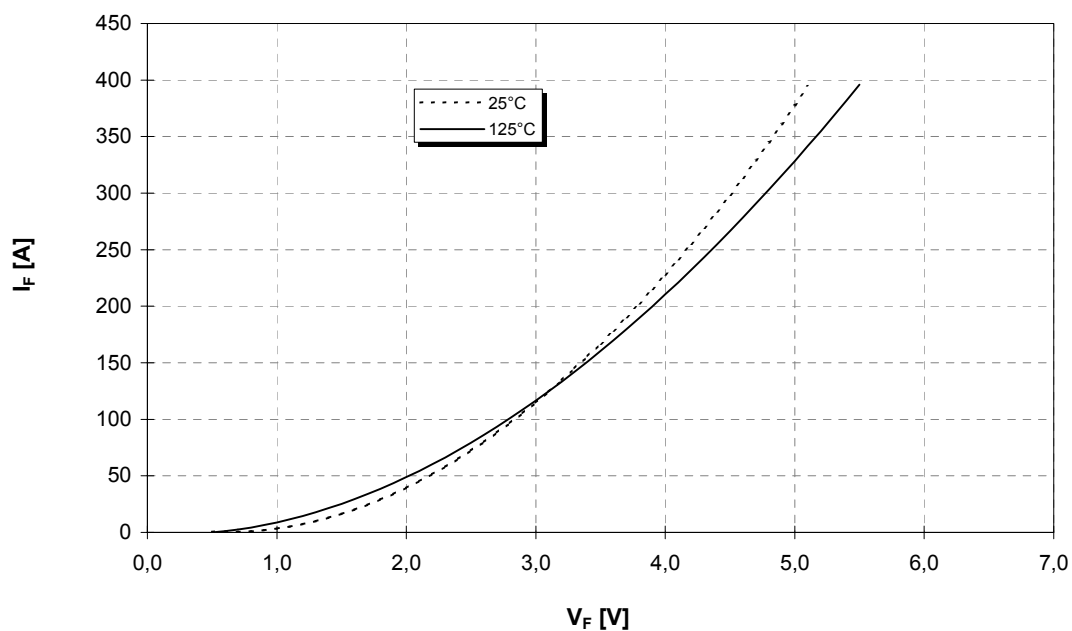
$$I_C = f(V_{GE})$$

$$V_{CE} = 10V$$



Durchlaßkennlinie der Inversdiode (typisch)
Forward characteristic of inverse diode (typical)

$$I_F = f(V_F)$$

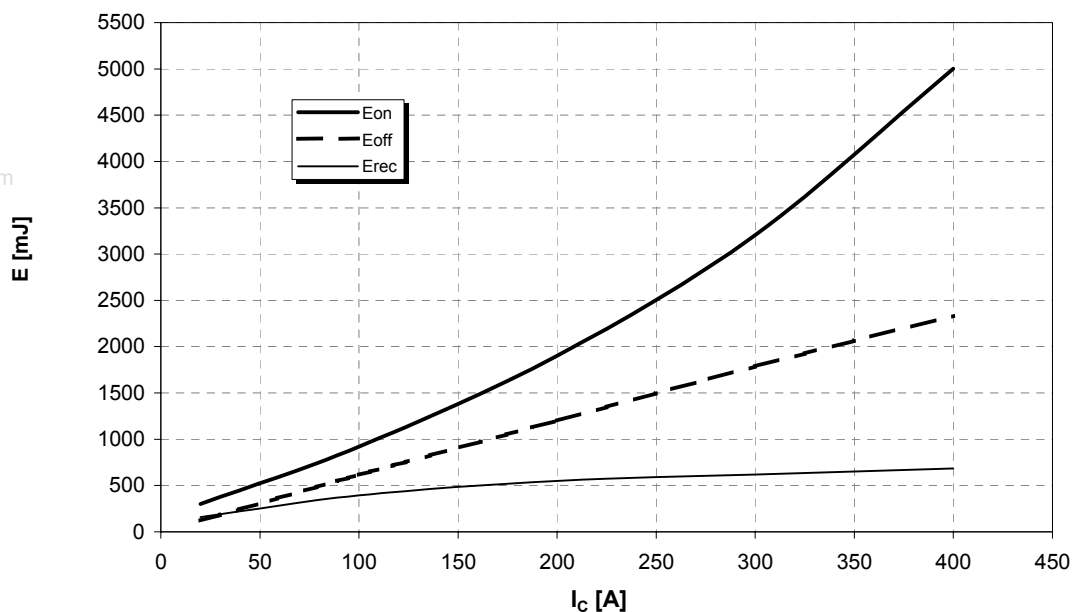




Schaltverluste (typisch) $E_{on} = f(I_C)$, $E_{off} = f(I_C)$, $E_{rec} = f(I_C)$

Switching losses (typical)

$R_{Gon}=13\Omega$, $R_{Goff}=75\Omega$, $C_{GE} = 22nF$, $V_{GE}=\pm 15V$, $V_{CE} = 3600V$, $T_{vj} = 125^\circ C$,

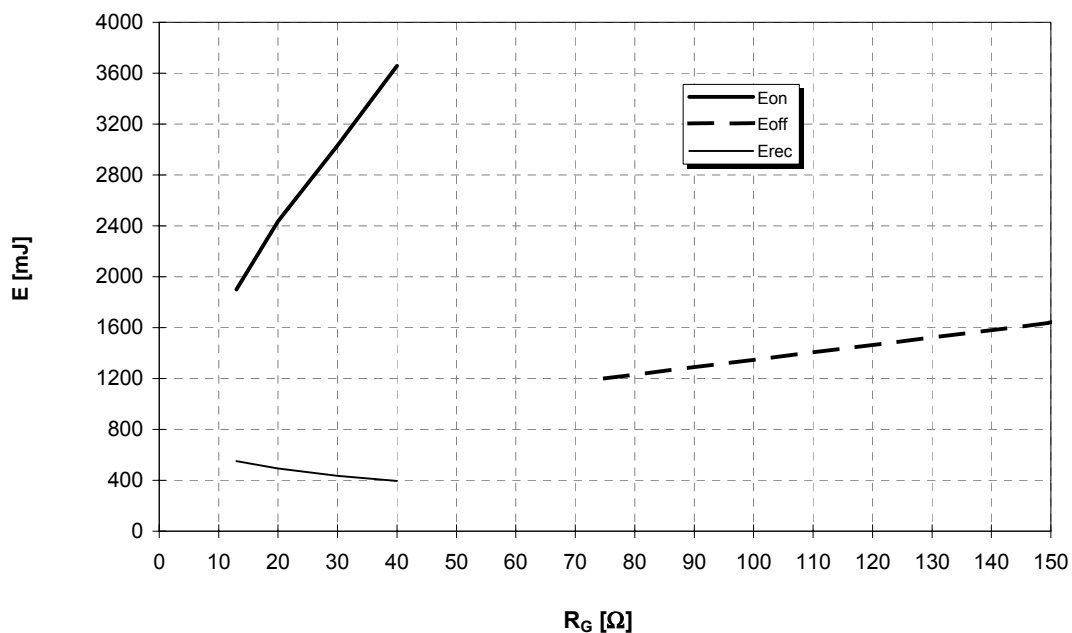


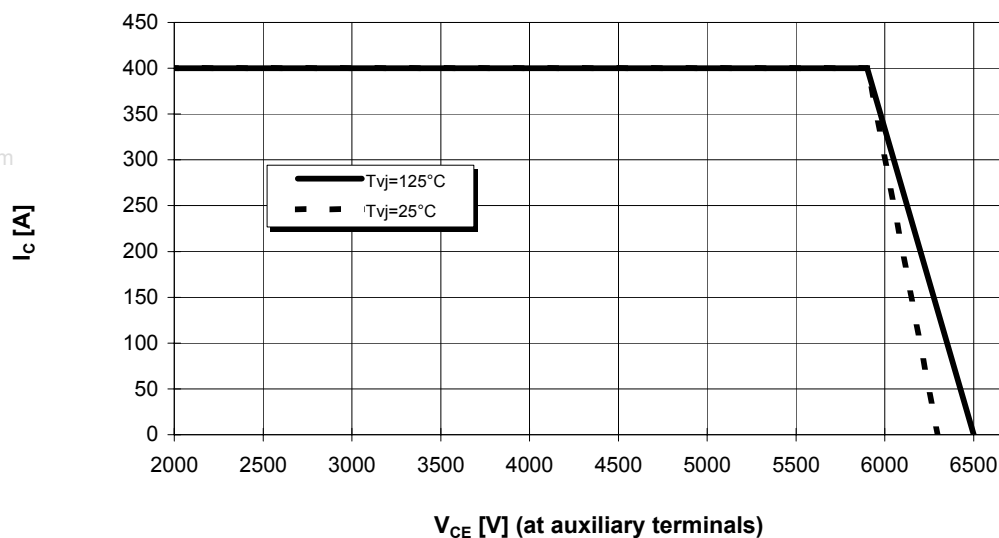
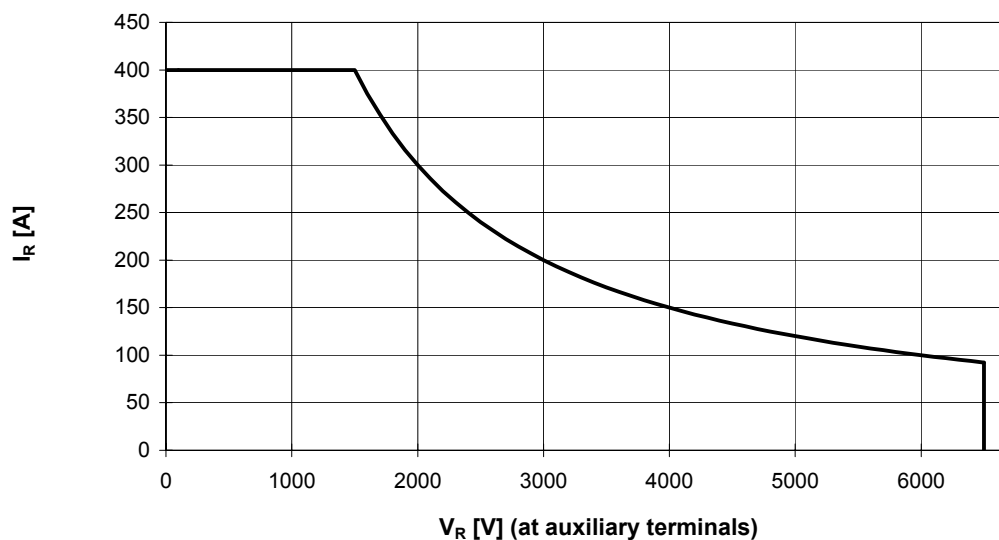
Schaltverluste (typisch)

$E_{on} = f(R_G)$, $E_{off} = f(R_G)$, $E_{rec} = f(R_G)$

Switching losses (typical)

$I_C = 200A$, $V_{CE} = 3600V$, $V_{GE}=\pm 15V$, $C_{GE}=22nF$, $T_{vj} = 125^\circ C$

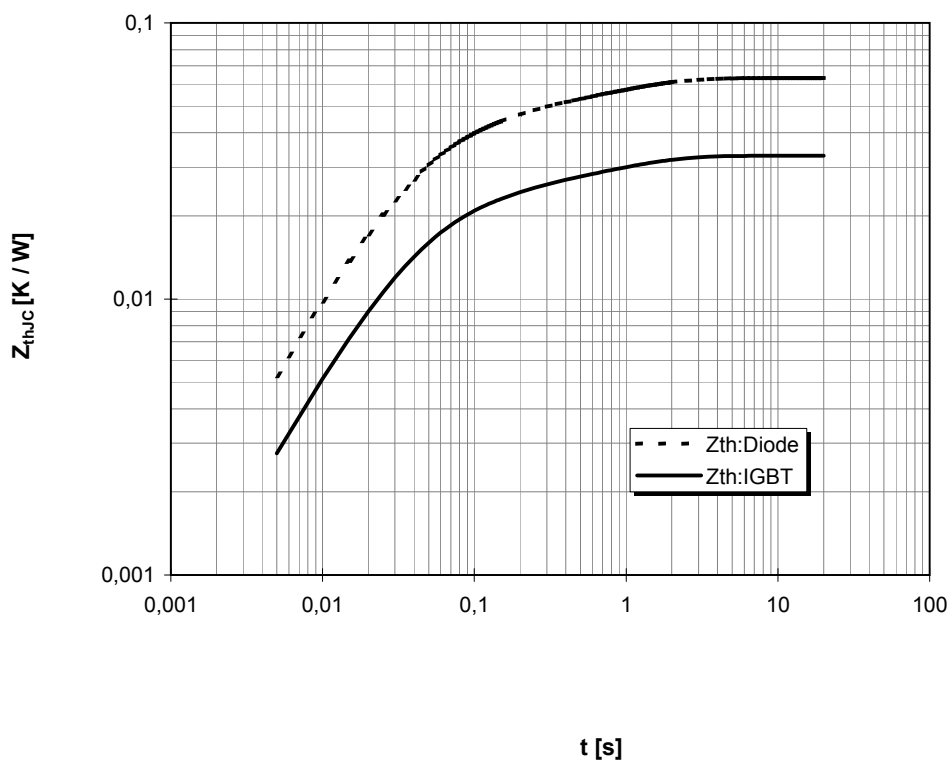


**Sicherer Arbeitsbereich (RBSOA)****Reverse bias safe operation area (RBSOA)** $R_{G,off} = 75\Omega$, $C_{GE} = 22nF$, $V_{GE} = \pm 15V$, $T_{vj} = <\text{see inset}>$, $V_{CC} \leq 4400V$ **Sicherer Arbeitsbereich Diode (SOA)****safe operation area Diode (SOA)** $P_{max} = 600kW$; $T_{vj} = 125^\circ C$ 



Transienter Wärmewiderstand
Transient thermal impedance

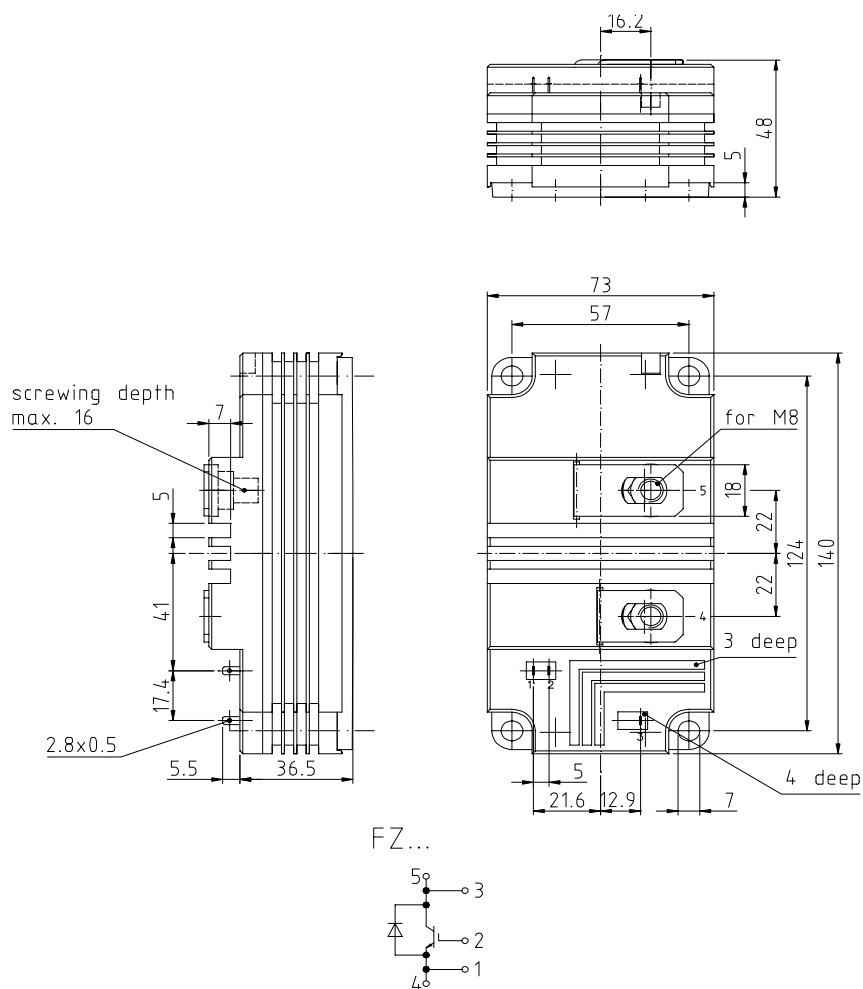
$$Z_{thJC} = f(t)$$



i		1	2	3	4
r_i [K/kW]	: IGBT	14,85	8,25	1,98	7,92
τ_i [s]	: IGBT	0,030	0,10	0,30	1,0
r_i [K/kW]	: Diode	28,35	15,75	3,78	15,12
τ_i [s]	: Diode	0,030	0,10	0,30	1,0



Äußere Abmessungen /
external dimensions



Anschlüsse / Terminals	1	Hilfsemitter / auxiliary emitter
	2	Gate / gate
	3	Hilfskollektor / auxiliary collector
	4	Emitter / emitter
	5	Kollektor / collector